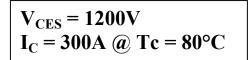
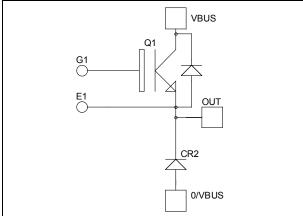
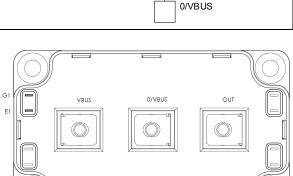


Buck chopper
High speed Trench + Field Stop
IGBT4 Power module







#### Application

- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- High speed Trench + Field Stop IGBT 4
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- M5 power connectors

#### **Benefits**

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS compliant

All ratings @  $T_i = 25$ °C unless otherwise specified

#### Absolute maximum ratings

1 2000111	· · · · · · · · · · · · · · · · · · ·			
Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	500	
$I_{C}$	Continuous Collector Current $T_C = 8$	$T_C = 80$ °C	300	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	960	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Power Dissipation		1500	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



#### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ , $V_{CE} =$			200	μΑ	
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C	1.78	2.05	2.42	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 300A$	$T_{j} = 150^{\circ}C$		2.6		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 10.4 \text{ mA}$		5.3	5.8	6.3	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V$ , $V_{CE} = 0V$				480	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$			17.6		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			1		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.9		
$Q_{G}$	Gate charge	$V_{GE} = 15V, I_{CE}$ $V_{CE} = 960V$	$V_{GE} = 15V, I_C = 300A$ $V_{CE} = 960V$		1290		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	tching (25°C)		30		ns
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			57		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 300A$			290		
$T_{\mathrm{f}}$	Fall Time	$R_G = 1.6\Omega$		16			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)			30		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			49		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 300A$			366		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 1.6\Omega$			48		
E <sub>on</sub>	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 150$ °C		26		mJ
$E_{\text{off}}$	Turn off Energy	$I_C = 300A$ $R_G = 1.6\Omega$	$T_j = 150$ °C		16		1113
$R_G$	Integrated gate resistor				2.5		Ω
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 600V$ $t_p \le 10\mu s$ ; $T_j = 150^{\circ}C$			1000		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.1	°C/W

Chopper diode ratings and characteristics

Symbol	Characteristic	naracteristic Test Conditions			Тур	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage					1200	V
$I_{RM}$	Reverse Leakage Current	V <sub>R</sub> =1200V				400	μΑ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		400		A
		$I_F = 400A$			2.4	3.5	
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 600A$			2.7		V
		$I_{\rm F} = 400 A$	$T_j = 125$ °C		1.8		
4	Reverse Recovery Time	$I_F = 400A$ $T_i =$	$T_j = 25^{\circ}C$		385		m.c
$t_{rr}$			$T_{j} = 125^{\circ}C$		480		ns
0	Reverse Recovery Charge	$\begin{array}{c} \text{V}_{\text{R}} = 800\text{V} \\ \text{di/dt} = 800\text{A/}\mu\text{s} \end{array}$	$T_i = 25^{\circ}C$		4.2		
$Q_{rr}$			$T_{j} = 125^{\circ}C$		21		μС
$R_{\text{thJC}}$	Junction to Case Thermal Resistance					0.096	°C/W



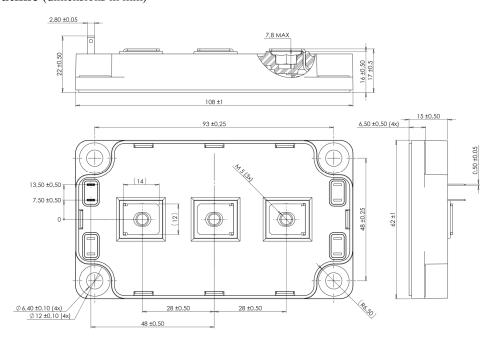
### IGBT parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage					1200	V
$I_{RM}$	Reverse Leakage Current	$V_R = 1200V$		•		100	μΑ
$I_F$	DC Forward Current		$Tc = 70^{\circ}C$		30		A
		$I_F = 30A$			2.6	3.5	
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 60A$	= 60A		3.2		V
		$I_F = 30A$	$T_{j} = 125^{\circ}C$		1.8		
_	Reverse Recovery Time	$I_F = 30A$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	$T_j = 25$ °C		300		200
$t_{rr}$			$T_{j} = 125^{\circ}C$		360		ns
Qrr	Reverse Recovery Charge	$\frac{V_R - 800 V}{\text{di/dt} = 200 \text{A/}\mu\text{s}}$	$T_j = 25$ °C		360		C
			$T_{j} = 125^{\circ}C$		1700		nC
$R_{thJC}$	Junction to Case Thermal Resistance					1.2	°C/W

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal	to case $t = 1 \min_{t \in S} \frac{1}{2}$	50/60Hz	4000		V
$T_{J}$	Operating junction temperature range				175	
$T_{JOP}$	Recommended junction temperature	under switching co	onditions	-40	T <sub>J</sub> max -25	°C
$T_{STG}$	Storage Temperature Range			-40	125	C
$T_{\rm C}$	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Torque	Wounting torque	For terminals	M5	2	3.5	
Wt	Package Weight				300	g

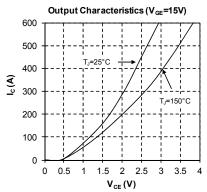
### Package outline (dimensions in mm)

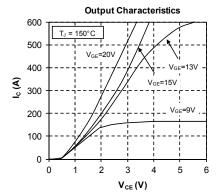


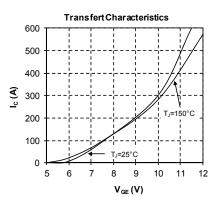
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

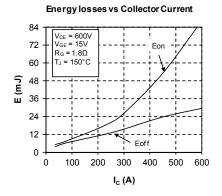


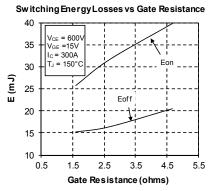
### Typical IGBT & chopper diode Performance Curve

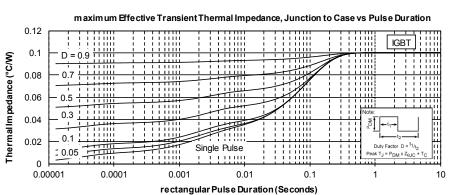




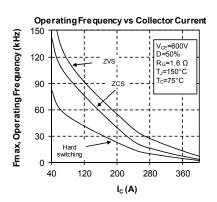


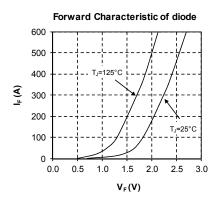


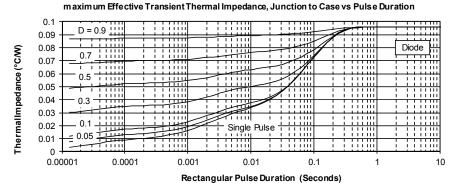




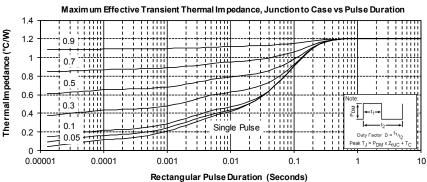


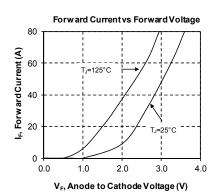






### IGBT parallel diode Typical Performance Curve







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